

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 8 A, 650 V, D2, D2PAK-2L

## FFSB0865B-F085

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 33 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

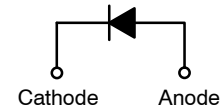
- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

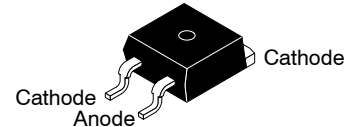
| Parameter                                                                                                | Symbol                                           | Value            | Unit |
|----------------------------------------------------------------------------------------------------------|--------------------------------------------------|------------------|------|
| Peak Repetitive Reverse Voltage                                                                          | V <sub>RRM</sub>                                 | 650              | V    |
| Single Pulse Avalanche Energy (T <sub>J</sub> = 25°C, I <sub>L(pk)</sub> = 11.5 A, L = 0.5 mH, V = 50 V) | E <sub>AS</sub>                                  | 33               | mJ   |
| Continuous Rectified Forward Current                                                                     | @ T <sub>C</sub> < 147                           | I <sub>F</sub>   | 8.0  |
|                                                                                                          | @ T <sub>C</sub> < 135                           |                  | 10.1 |
| Non-Repetitive Peak Forward Surge Current                                                                | T <sub>C</sub> = 25°C<br>t <sub>p</sub> = 10 μs  | I <sub>FM</sub>  | 577  |
|                                                                                                          | T <sub>C</sub> = 150°C<br>t <sub>p</sub> = 10 μs |                  | 533  |
| Non-Repetitive Forward Surge Current (Half-Sine Pulse)                                                   | T <sub>C</sub> = 25°C<br>t <sub>p</sub> = 8.3 ms | I <sub>FSM</sub> | 56   |
| Power Dissipation                                                                                        | T <sub>C</sub> = 25°C                            | P <sub>tot</sub> | 73   |
|                                                                                                          | T <sub>C</sub> = 150°C                           |                  | 12   |
| Operating Junction and Storage Temperature Range                                                         | T <sub>J</sub> , T <sub>stg</sub>                | -55 to +175      | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

|                  |                |
|------------------|----------------|
| V <sub>RRM</sub> | I <sub>F</sub> |
| 650 V            | 8.0 A          |

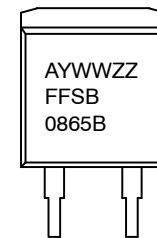


Schottky Diode



D2PAK2 (TO-263-2L)  
CASE 418BK

### MARKING DIAGRAM



- |           |                           |
|-----------|---------------------------|
| A         | = Assembly Plant Code     |
| YWW       | = Date Code (Year & Week) |
| ZZ        | = Lot Code                |
| FFSB0865B | = Specific Device Code    |

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSB0865B–F085

## THERMAL CHARACTERISTICS

| Parameter                                  | Symbol          | Value | Unit |
|--------------------------------------------|-----------------|-------|------|
| Thermal Resistance, Junction–to–Case, Max. | $R_{\theta JC}$ | 2.05  | °C/W |

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------|--------|-----------------|-----|-----|-----|------|
|-----------|--------|-----------------|-----|-----|-----|------|

### ON CHARACTERISTICS

|                 |       |                                               |  |      |     |               |
|-----------------|-------|-----------------------------------------------|--|------|-----|---------------|
| Forward Voltage | $V_F$ | $I_F = 8.0\text{ A}, T_J = 25^\circ\text{C}$  |  | 1.39 | 1.7 | V             |
|                 |       | $I_F = 8.0\text{ A}, T_J = 125^\circ\text{C}$ |  | 1.55 | 2.0 |               |
|                 |       | $I_F = 8.0\text{ A}, T_J = 175^\circ\text{C}$ |  | 1.71 | 2.4 |               |
| Reverse Current | $I_R$ | $V_R = 650\text{ V}, T_J = 25^\circ\text{C}$  |  | 0.5  | 40  | $\mu\text{A}$ |
|                 |       | $V_R = 650\text{ V}, T_J = 125^\circ\text{C}$ |  | 1.0  | 80  |               |
|                 |       | $V_R = 650\text{ V}, T_J = 175^\circ\text{C}$ |  | 2.0  | 160 |               |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                         |           |                                          |  |     |  |    |
|-------------------------|-----------|------------------------------------------|--|-----|--|----|
| Total Capacitive Charge | $Q_C$     | $V_C = 400\text{ V}$                     |  | 22  |  | nC |
|                         | $C_{tot}$ | $V_R = 1\text{ V}, f = 100\text{ kHz}$   |  | 336 |  | pF |
|                         |           | $V_R = 200\text{ V}, f = 100\text{ kHz}$ |  | 39  |  |    |
|                         |           | $V_R = 400\text{ V}, f = 100\text{ kHz}$ |  | 30  |  |    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## PACKAGE MARKING AND ORDERING INFORMATION

| Part Number    | Top Marking | Package                            | Packing Method | Reel Size | Tape Width | Quantity  |
|----------------|-------------|------------------------------------|----------------|-----------|------------|-----------|
| FFSB0865B–F085 | FFSB0865B   | D <sup>2</sup> PAK2<br>(TO–263–2L) | Tape & Reel†   | 330 mm    | 24 mm      | 800 Units |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

## TYPICAL CHARACTERISTICS

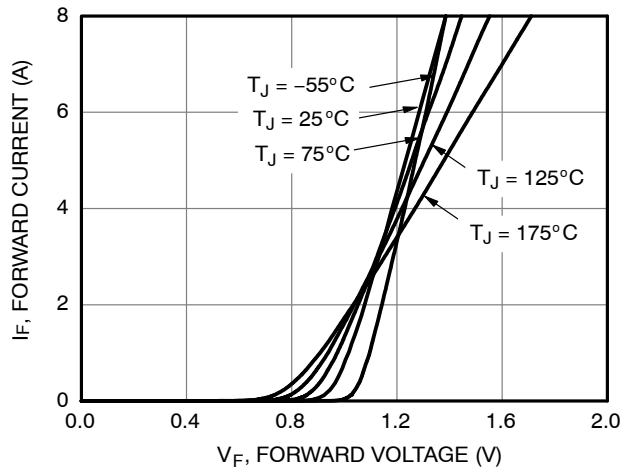


Figure 1. Forward Characteristics

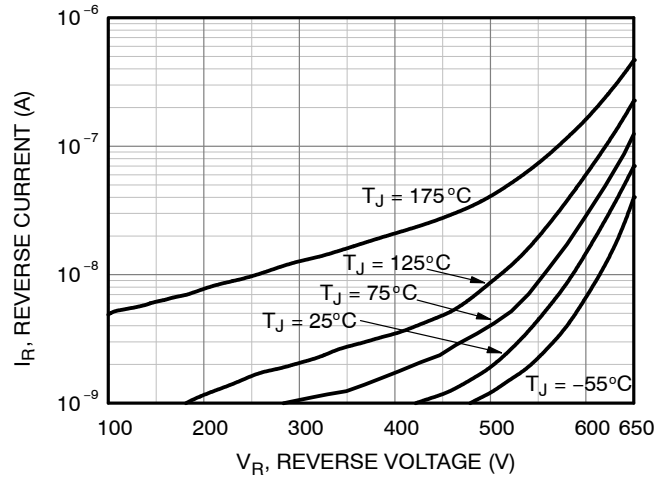


Figure 2. Reverse Characteristics

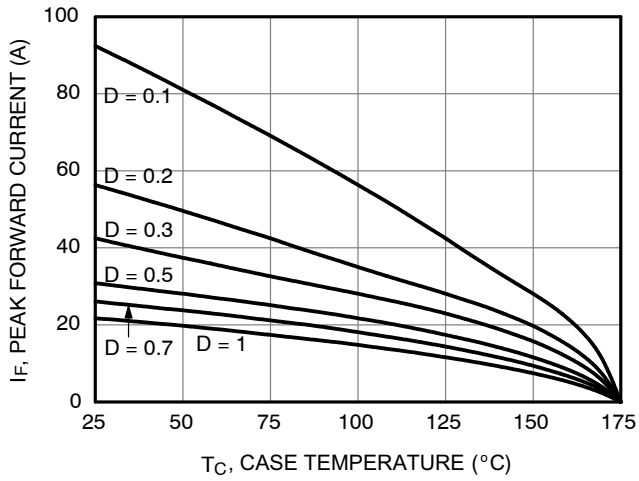


Figure 3. Current Derating

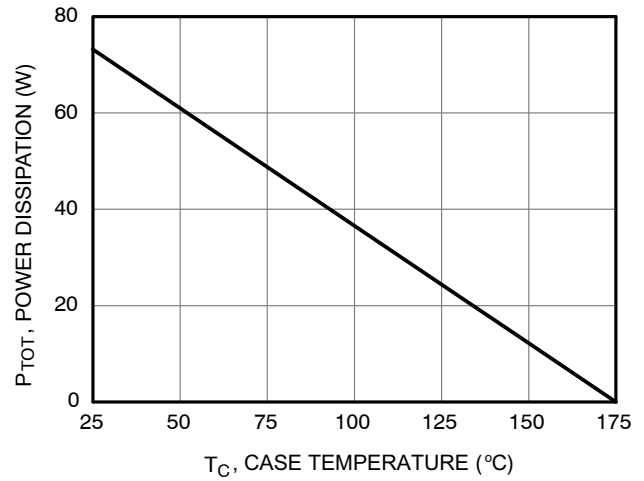


Figure 4. Power Derating

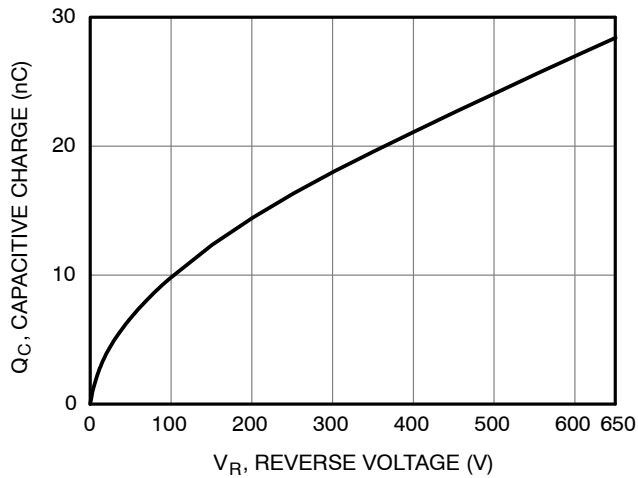


Figure 5. Capacitive Charge vs. Reverse Voltage

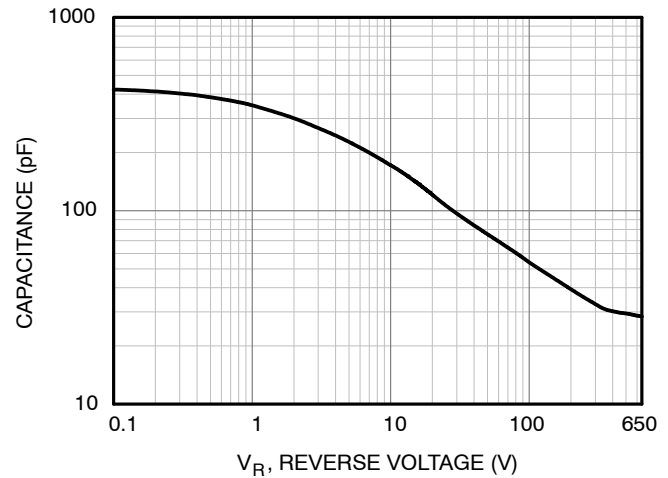


Figure 6. Capacitance vs. Reverse Voltage

## TYPICAL CHARACTERISTICS

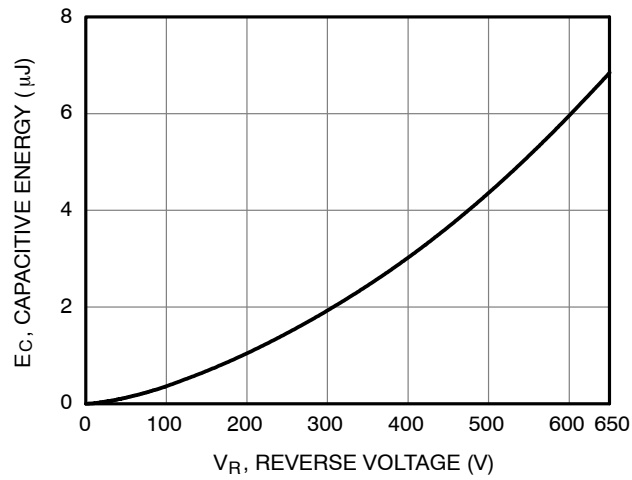


Figure 7. Capacitance Stored Energy

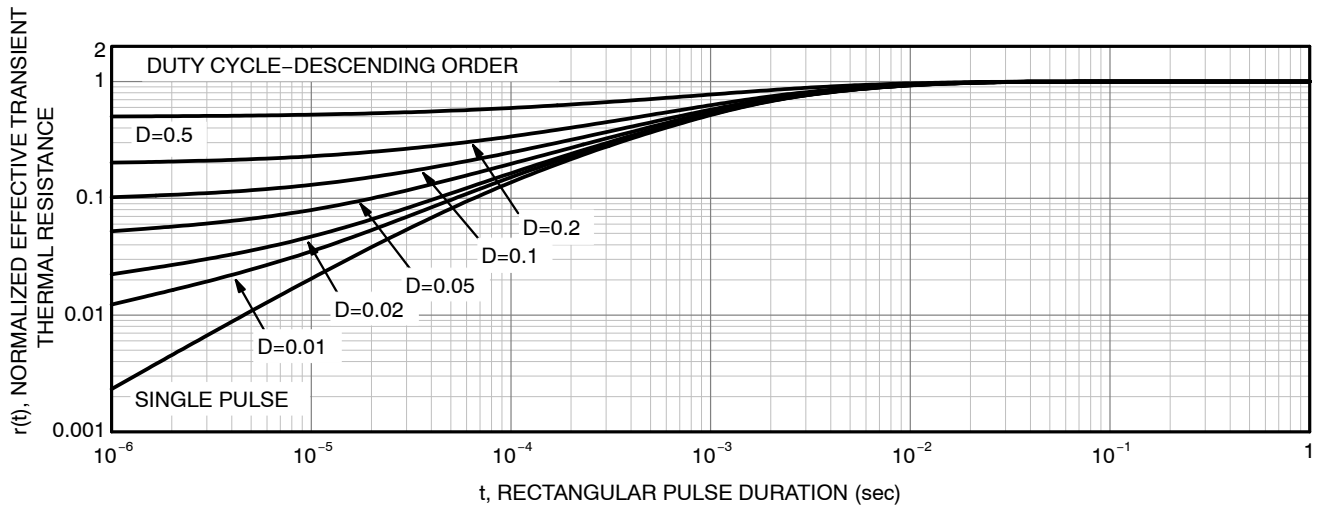
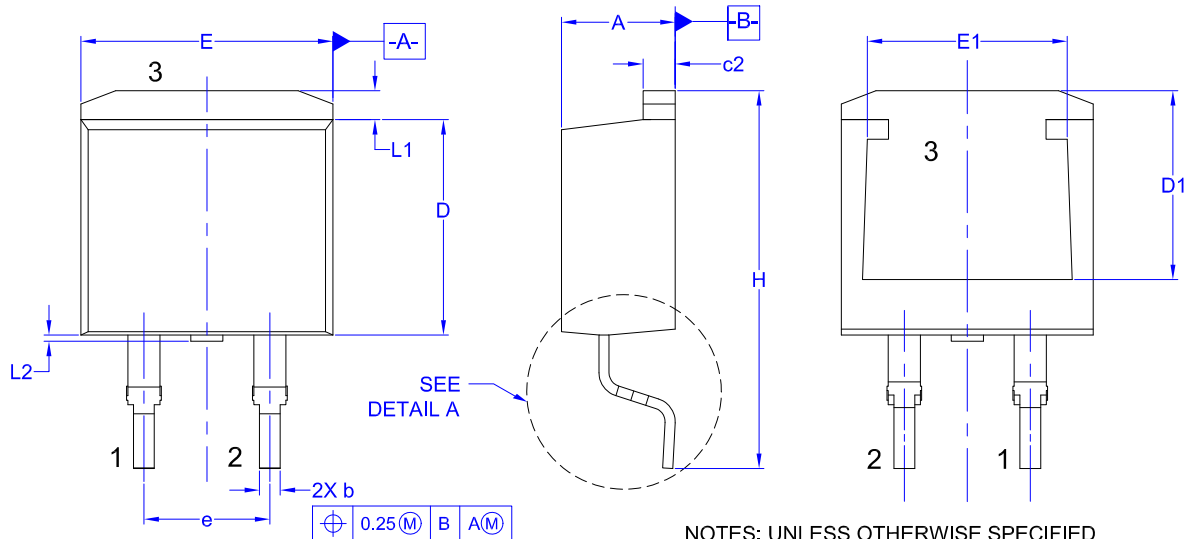
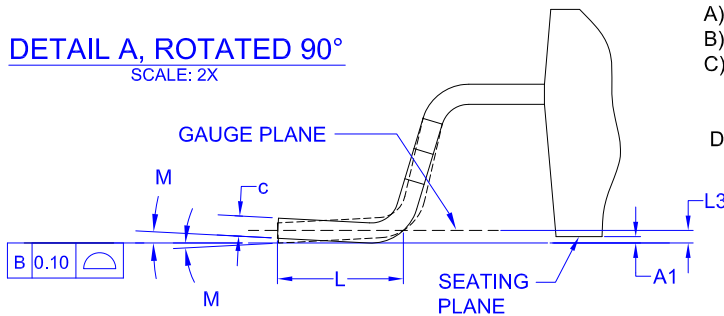
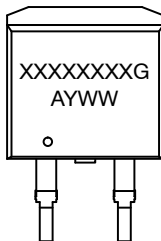


Figure 8. Junction-to-Case Transient Thermal Response

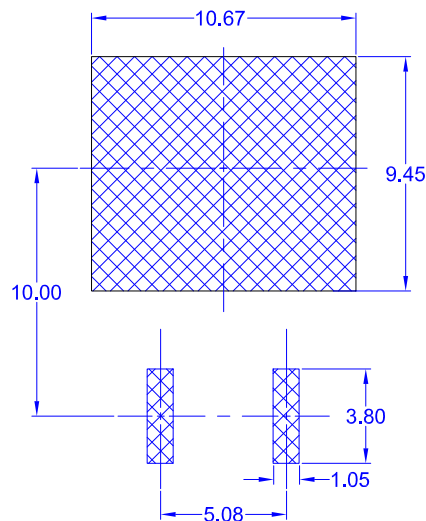

**D<sup>2</sup>PAK2 (TO-263-2L)**  
CASE 418BK  
ISSUE O

DATE 02 AUG 2018


**DETAIL A, ROTATED 90°**  
SCALE: 2X

**GENERIC MARKING DIAGRAM\***


XXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


**LAND PATTERN RECOMMENDATION**  
UNLESS NOTED, ALL DIMS TYPICAL

NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.

B) REFERENCE JEDEC, TO-263, VARIATION AB.

C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.

D) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N

| DIM | MILLIMETERS |       |       |
|-----|-------------|-------|-------|
|     | MIN         | NOM   | MAX   |
| A   | 4.06        | 4.57  | 4.83  |
| A1  | 0.00        | 0.10  | 0.25  |
| b   | 0.51        | 0.81  | 0.99  |
| c   | 0.30        | 0.407 | 0.74  |
| c2  | 1.14        | 1.30  | 1.65  |
| D   | 8.38        | 8.69  | 9.65  |
| D1  | 7.30        | 7.80  | 8.30  |
| E   | 9.65        | 10.16 | 10.67 |
| E1  | 8.00        | 8.62  | 9.00  |
| e   | 5.08 BSC    |       |       |
| H   | 14.60       | 15.35 | 15.88 |
| L   | 1.78        | 2.54  | 2.79  |
| L1  | 0.90        | 1.29  | 1.68  |
| L2  | 0.00        | 0.15  | 0.25  |
| L3  | 0.25 BSC    |       |       |
| M   | 0°          | 4°    | 8°    |

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**DESCRIPTION:** D<sup>2</sup>PAK2 (TO-263-2L)

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